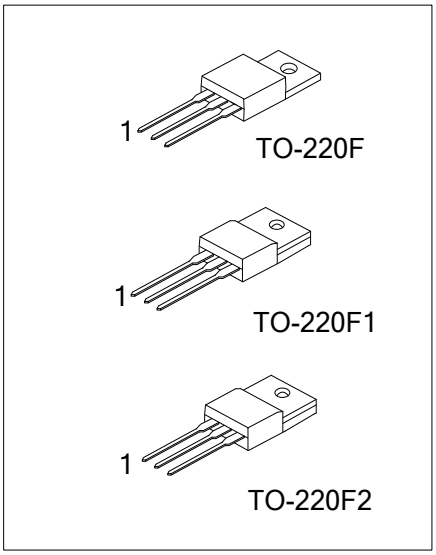
# 8N90-LC

**Preliminary** ***Power MOSFET***

## 8A, 900V N-CHANNEL POWER MOSFET



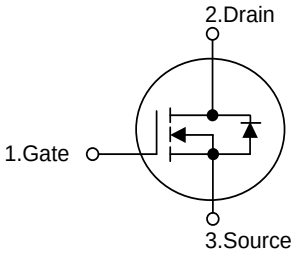

### ■ DESCRIPTION

The UTC **8N90-LC** is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.

### ■ FEATURES

* $R_{DS(ON)} \leq 2.1\ \Omega$ @ $V_{GS}$=10V, $I_D$=4.0A
* Fast switching capability
* Avalanche energy tested
* Improved dv/dt capability, high ruggedness

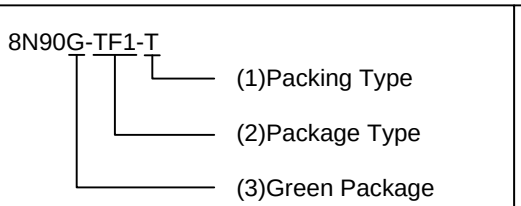
### ■ SYMBOL




### ■ ORDERING INFORMATION

| Ordering Number | | Package | Pin Assignment | | | Packing |
|---|---|---|---|---|---|---|
| Lead Free | Halogen Free | | 1 | 2 | 3 | |
| 8N90L-TF1-T | 8N90G-TF1-T | TO-220F1 | G | D | S | Tube |
| 8N90L-TF2-T | 8N90G-TF2-T | TO-220F2 | G | D | S | Tube |
| 8N90L-TF3-T | 8N90G-TF3-T | TO-220F | G | D | S | Tube |

Note: Pin Assignment: G: Gate D: Drain S: Source

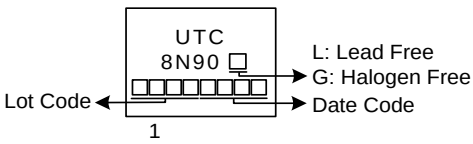



(1) T: Tube

(2) TF1: TO-220F1, TF2: TO-220F2, TF3: TO-220F

(3) G: Halogen Free and Lead Free, L: Lead Free

### ■ MARKING



## ■ ABSOLUTE MAXIMUM RATINGS ($T_C$=25°C, unless otherwise specified)

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|---|---|---|---|---|
| Drain-Source Voltage | | $V_{DSS}$ | 900 | V |
| Gate-Source Voltage | | $V_{GSS}$ | ±30 | V |
| Continuous Drain Current | | $I_D$ | 8 | A |
| Pulsed Drain Current (Note 2) | | $I_{DM}$ | 16 | A |
| Avalanche Energy | Single Pulsed (Note 3) | $E_{AS}$ | 336 | mJ |
| Peak Diode Recovery dv/dt (Note 4) | | dv/dt | 2.2 | V/ns |
| Power Dissipation | | $P_D$ | 38 | W |
| Junction Temperature | | $T_J$ | +150 | °C |
| Storage Temperature | | $T_{STG}$ | -55 ~ +150 | °C |

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 30mH, $I_{AS}$ = 4.73A, $V_{DD}$ = 100V, $R_G$ = 25 Ω, Starting $T_J$ = 25°C
4. $I_{SD}$ ≤ 8.0A, di/dt ≤ 200A/μs, $V_{DD}$ ≤ $BV_{DSS}$, Starting $T_J$ = 25°C

## ■ THERMAL DATA

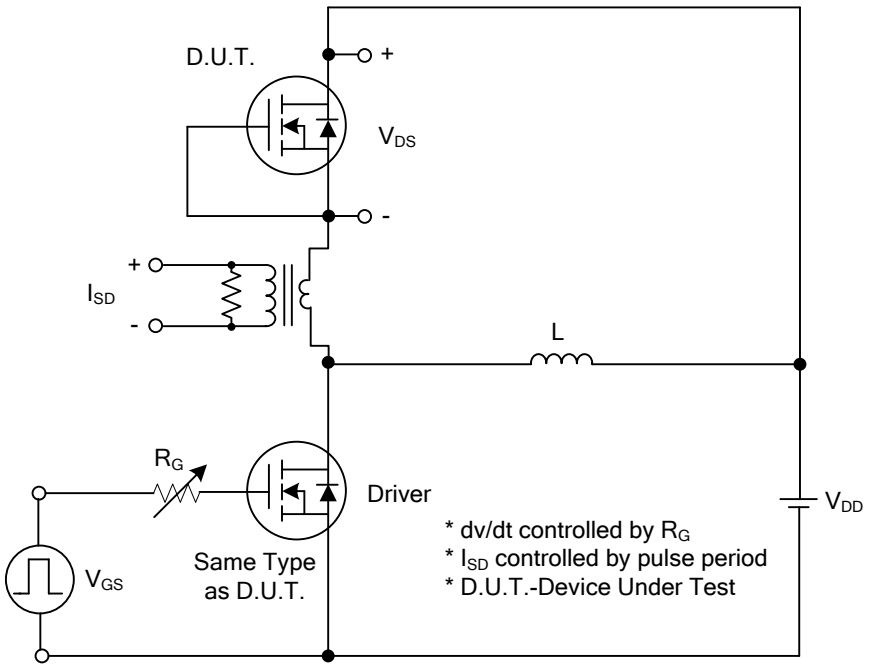
| PARAMETER | SYMBOL | RATING | UNIT |
|---|---|---|---|
| Junction to Ambient | $\theta_{JA}$ | 62.5 | °C/W |
| Junction to Case | $\theta_{JC}$ | 3.28 | °C/W |

## ■ ELECTRICAL CHARACTERISTICS ($T_J$=25°C, unless otherwise specified)

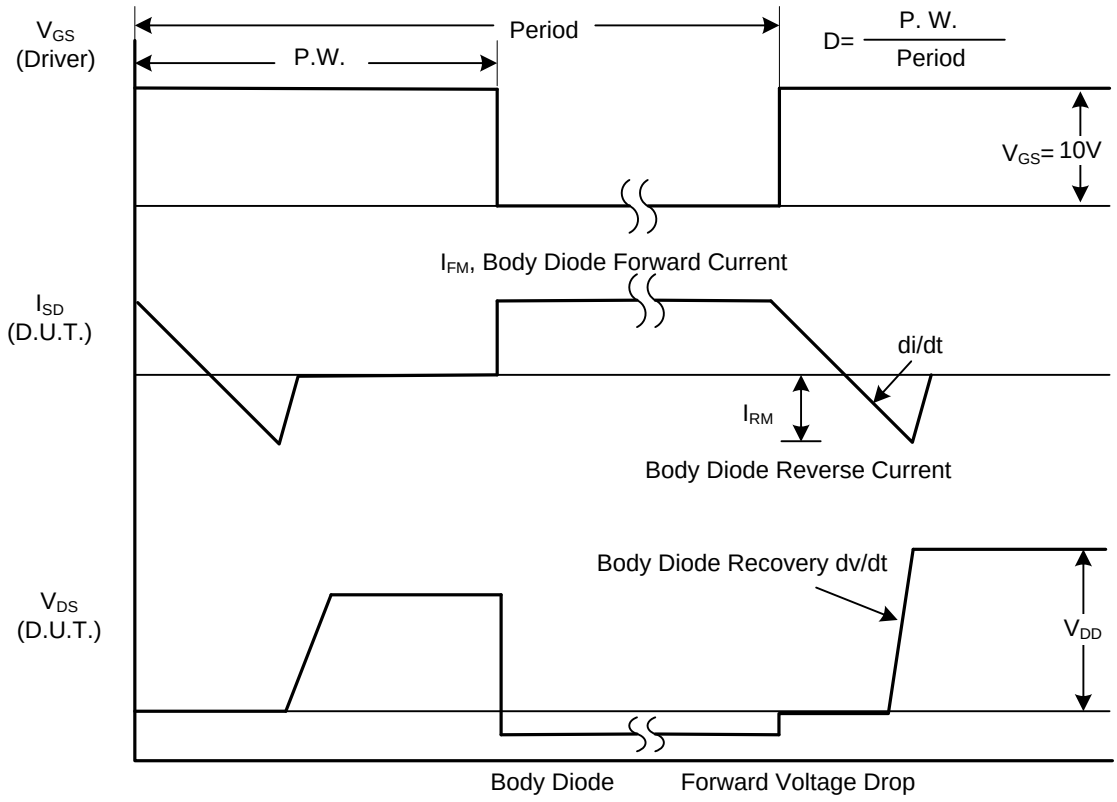
| PARAMETER | | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | | |
| Drain-Source Breakdown Voltage | | $BV_{DSS}$ | $V_{GS}$=0V, $I_D$=250μA | 900 | | | V |
| Drain-Source Leakage Current | | $I_{DSS}$ | $V_{DS}$=900V, $V_{GS}$=0V | | | 10 | μA |
| Gate- Source Leakage Current | Forward | $I_{GSS}$ | $V_{GS}$=30V, $V_{DS}$=0V | | | 100 | nA |
| | Reverse | | $V_{GS}$=-30V, $V_{DS}$=0V | | | -100 | nA |
| **ON CHARACTERISTICS** | | | | | | | |
| Gate Threshold Voltage | | $V_{GS(TH)}$ | $V_{DS}$=$V_{GS}$, $I_D$=250μA | 3.0 | | 5.0 | V |
| Static Drain-Source On-State Resistance | | $R_{DS(ON)}$ | $V_{GS}$=10V, $I_D$=4.0A | | | 2.1 | Ω |
| **DYNAMIC CHARACTERISTICS** | | | | | | | |
| Input Capacitance | | $C_{ISS}$ | $V_{DS}$=25V, $V_{GS}$=0V, f=1.0MHz | | 1390 | | pF |
| Output Capacitance | | $C_{OSS}$ | | | 120 | | pF |
| Reverse Transfer Capacitance | | $C_{RSS}$ | | | 8 | | pF |
| **SWITCHING CHARACTERISTICS** | | | | | | | |
| Total Gate Charge (Note 1) | | $Q_G$ | $V_{DS}$=720V, $V_{GS}$=10V, $I_D$=8A $I_G$=1mA (Note 1, 2) | | 36 | | nC |
| Gate-Source Charge | | $Q_{GS}$ | | | 14 | | nC |
| Gate-Drain Charge | | $Q_{GD}$ | | | 9.6 | | nC |
| Turn-On Delay Time (Note 1) | | $t_{D(ON)}$ | $V_{DS}$=100V, $V_{GS}$=10V, $I_D$=8A, $R_G$=25Ω (Note 1, 2) | | 26 | | ns |
| Turn-On Rise Time | | $t_R$ | | | 19 | | ns |
| Turn-Off Delay Time | | $t_{D(OFF)}$ | | | 84 | | ns |
| Turn-Off Fall Time | | $t_F$ | | | 38 | | ns |
| **DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS** | | | | | | | |
| Maximum Body-Diode Continuous Current | | $I_S$ | | | | 8 | A |
| Maximum Body-Diode Pulsed Current | | $I_{SM}$ | | | | 16 | A |
| Drain-Source Diode Forward Voltage (Note 1) | | $V_{SD}$ | $I_S$=8A , $V_{GS}$=0V | | | 1.4 | V |
| Reverse Recovery Time (Note 1) | | $t_{rr}$ | $I_S$=8A , $V_{GS}$=0V di/dt=100A/μs | | 540 | | ns |
| Reverse Recovery Charge | | $Q_{rr}$ | | | 13.5 | | μC |

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

## ■ TEST CIRCUITS AND WAVEFORMS

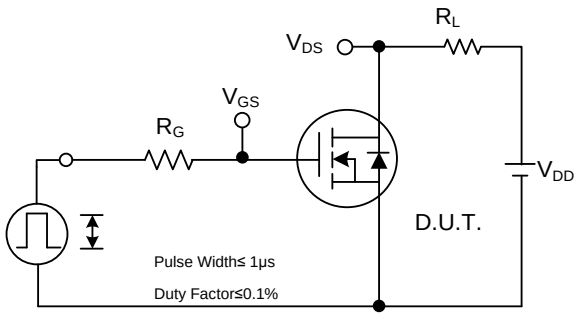



**Peak Diode Recovery dv/dt Test Circuit**

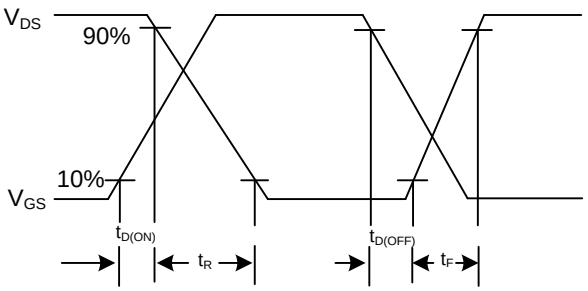



**Peak Diode Recovery dv/dt Waveforms**

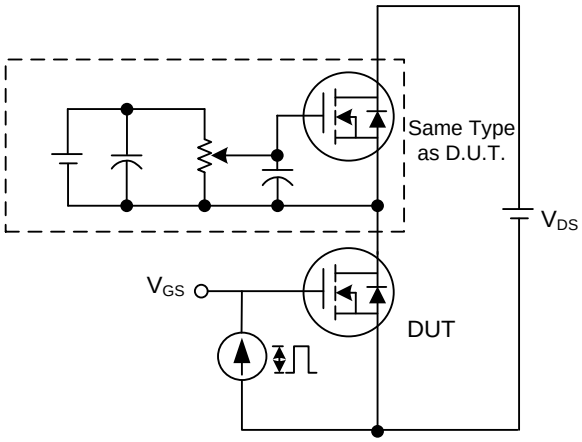
## ■ TEST CIRCUITS AND WAVEFORMS



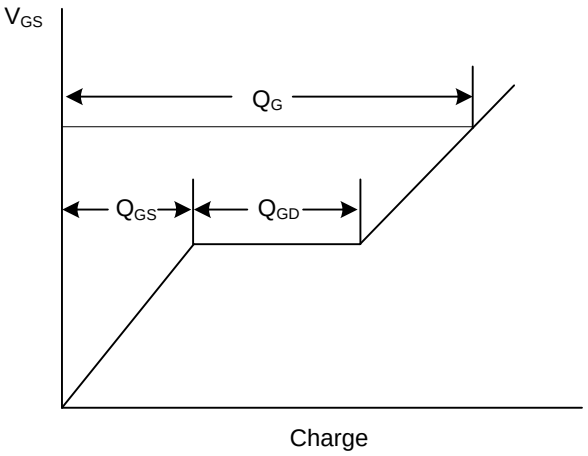

**Switching Test Circuit**



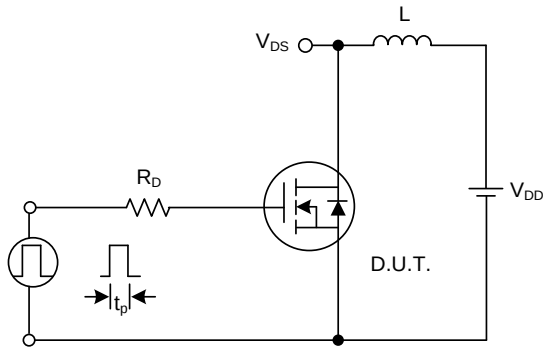

**Switching Waveforms**



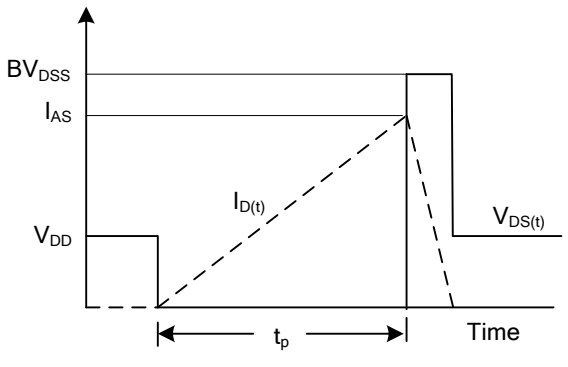

**Gate Charge Test Circuit**




**Gate Charge Waveform**




**Unclamped Inductive Switching Test Circuit**




**Unclamped Inductive Switching Waveforms**